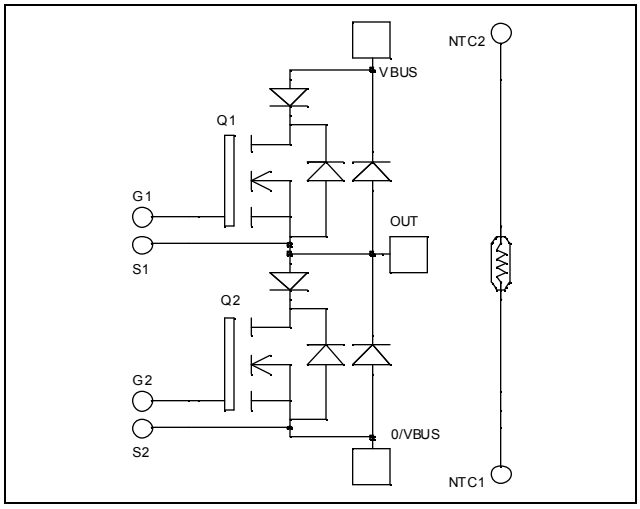
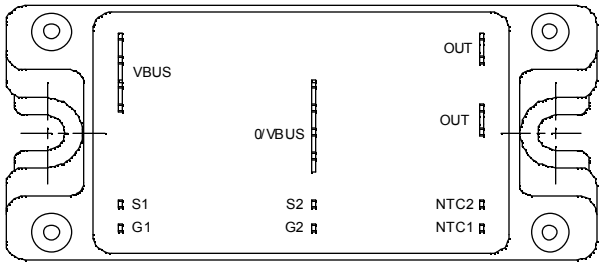
APTM100A23STG

Phase leg
Series & parallel diodes
MOSFET Power Module

V_{DSS} = 1000V
R_{DSon} = 230mΩ typ @ Tj = 25°C
I_D = 36A @ Tc = 25°C





Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7® MOSFETs
  - Low R_{DSon}
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		1000	V
I_D	Continuous Drain Current	T_c = 25°C	36	A
		T_c = 80°C	27	
I_{DM}	Pulsed Drain current		144	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		270	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	694	W
I_{AR}	Avalanche current (repetitive and non repetitive)		18	A
E_{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		2500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS}= 1000V	T_j = 25°C			200	µA
		V_{GS} = 0V, V_{DS}= 800V	T_j = 125°C			1000	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 18A			230	270	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 5mA		3		5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±30 V, V_{DS} = 0V				±150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		8700		pF
C_{oss}	Output Capacitance			1430		
C_{rss}	Reverse Transfer Capacitance			240		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 500V I_D = 36A		308		nC
Q_{gs}	Gate – Source Charge			52		
Q_{gd}	Gate – Drain Charge			194		
$T_{d(on)}$	Turn-on Delay Time	**Inductive switching @ 125°C** V_{GS} = 15V V_{Bus} = 667V I_D = 36A R_G = 2.5Ω		10		ns
T_r	Rise Time			12		
$T_{d(off)}$	Turn-off Delay Time			121		
T_f	Fall Time			35		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 667V I_D = 36A, R_G = 2.5Ω		1278		µJ
E_{off}	Turn-off Switching Energy			760		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 667V I_D = 36A, R_G = 2.5Ω		2092		µJ
E_{off}	Turn-off Switching Energy			902		

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=200V	T_j = 25°C			350	µA
			T_j = 125°C			600	
I_F	DC Forward Current		T_c = 85°C		60		A
V_F	Diode Forward Voltage	I_F = 60A			1.1	1.15	V
		I_F = 120A			1.4		
		I_F = 60A	T_j = 125°C		0.9		
t_{rr}	Reverse Recovery Time	I_F = 60A V_R = 133V di/dt = 400A/µs	T_j = 25°C		24		ns
			T_j = 125°C		48		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		66		nC
			T_j = 125°C		300		

Parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1000			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1000V	T_j = 25°C			350	µA
			T_j = 125°C			600	
I_F	DC Forward Current		T_c = 65°C		60		A
V_F	Diode Forward Voltage	I_F = 60A			1.9	2.3	V
		I_F = 120A			2.2		
		I_F = 60A	T_j = 125°C		1.7		
t_{rr}	Reverse Recovery Time	I_F = 60A V_R = 667V di/dt = 400A/µs	T_j = 25°C		290		ns
			T_j = 125°C		390		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		1340		nC
			T_j = 125°C		4700		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		Transistor			0.18	°C/W
			Diode			0.65	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

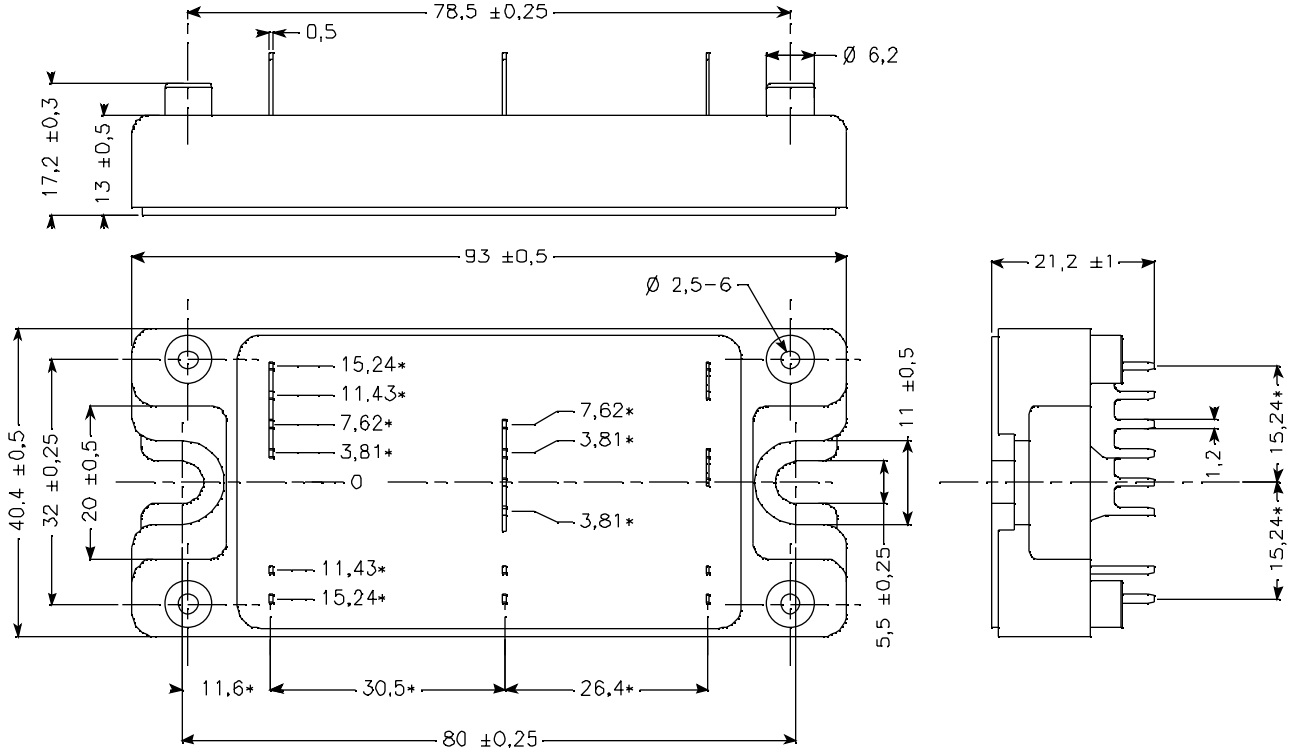
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		50		kΩ
$B_{25/85}$	T_{25} = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

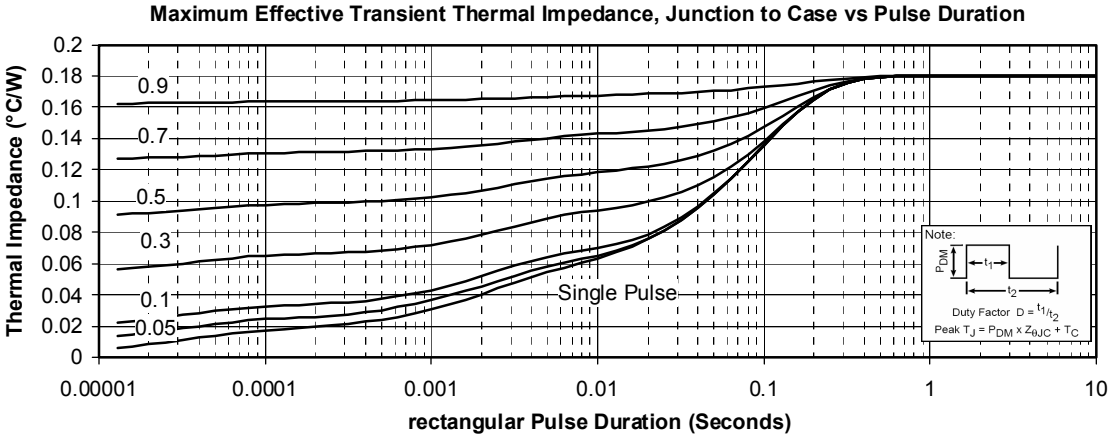
T: Thermistor temperature
R_T: Thermistor value at T

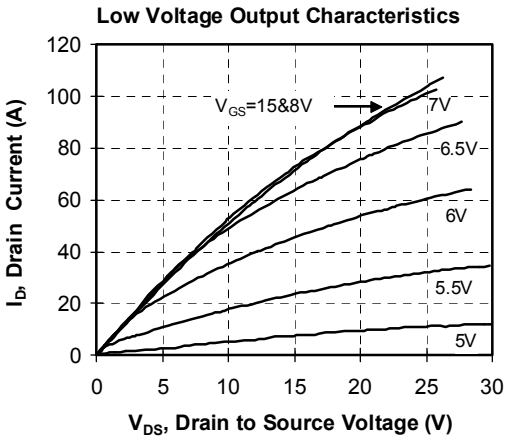
SP4 Package outline (dimensions in mm)

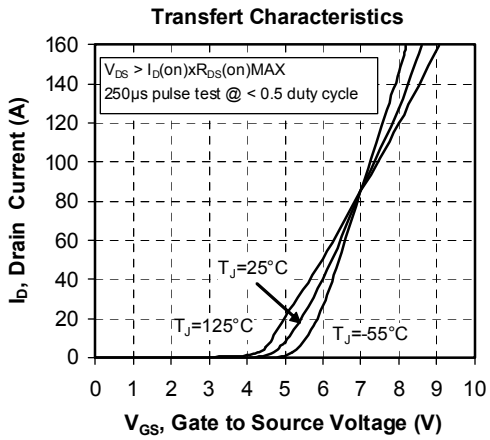


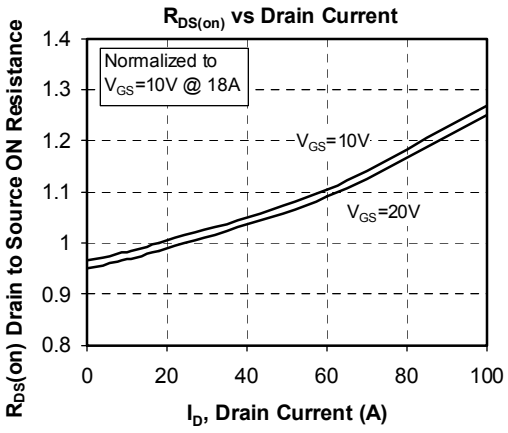
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

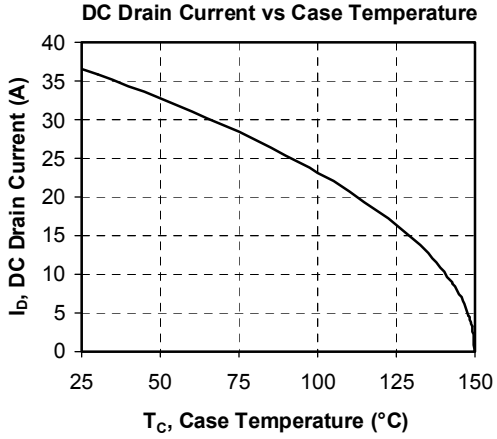
Typical Performance Curve



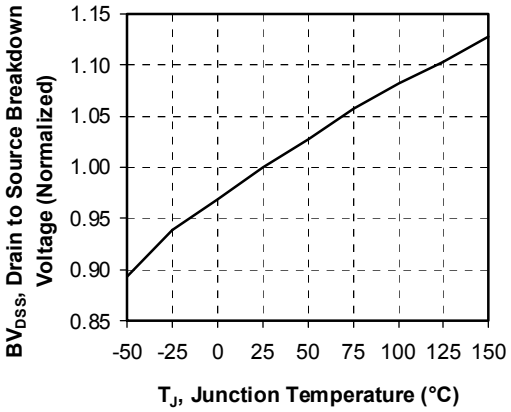




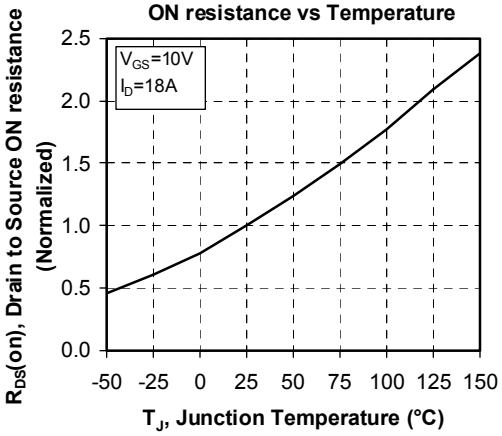




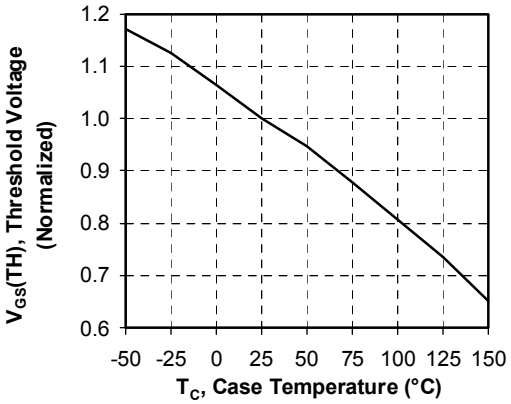
Breakdown Voltage vs Temperature



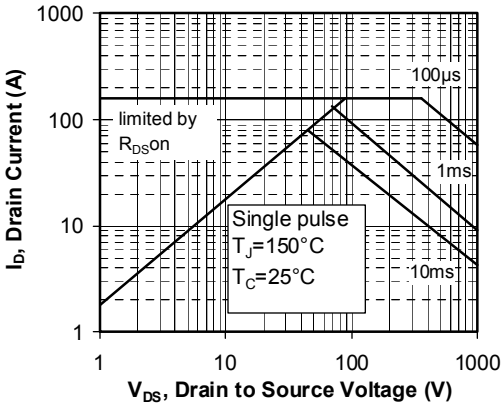
ON resistance vs Temperature



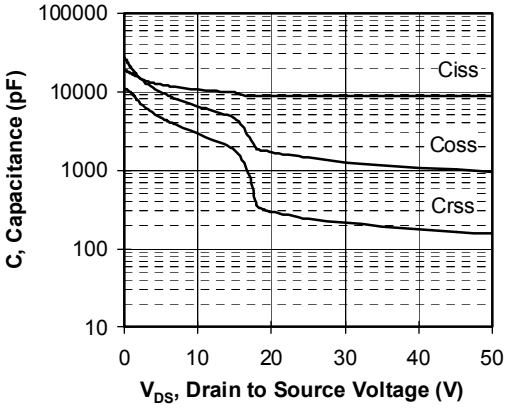
Threshold Voltage vs Temperature



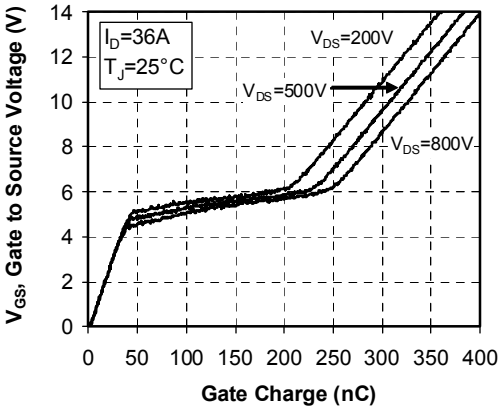
Maximum Safe Operating Area



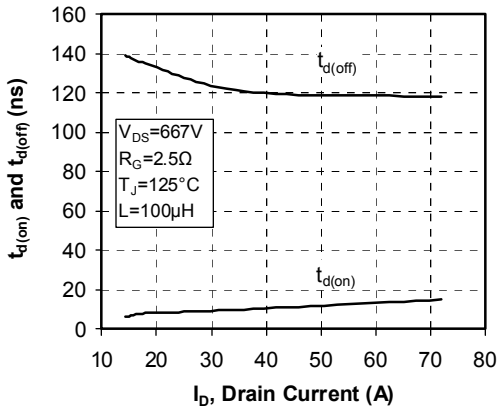
Capacitance vs Drain to Source Voltage



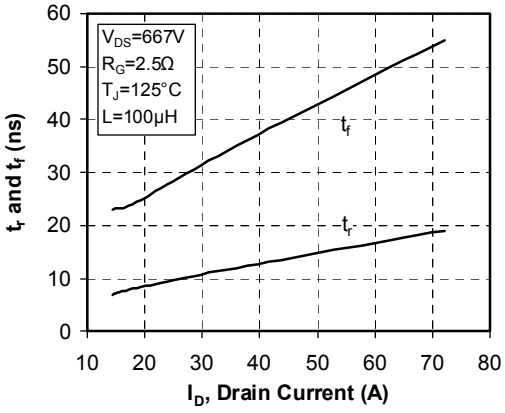
Gate Charge vs Gate to Source Voltage



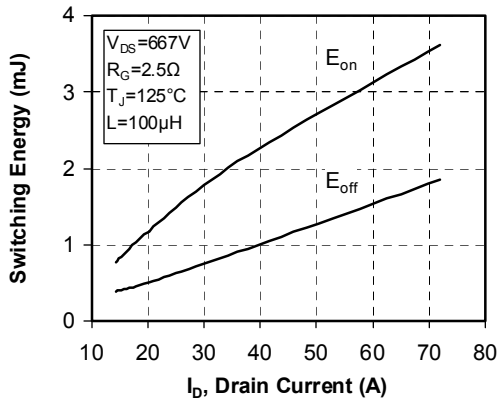
Delay Times vs Current



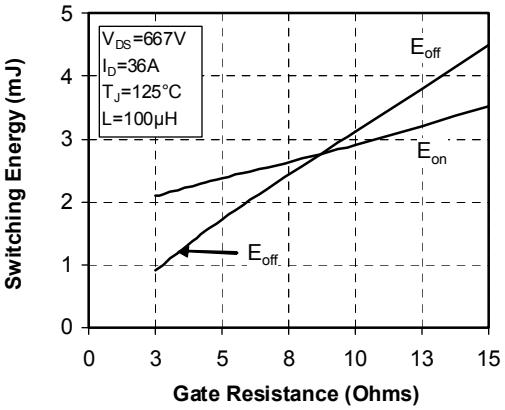
Rise and Fall times vs Current



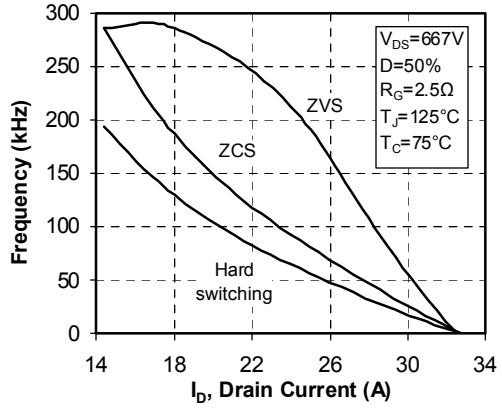
Switching Energy vs Current



Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage